

METHOD OF FABRICATING NON-VOLATILE MEMORY DEVICE

ABSTRACT OF THE DISCLOSURE

5 A method of fabricating a non-volatile memory device includes the steps of forming a lower conductive layer on a substrate, forming a lower and an upper sacrificial patterns on the substrate with the lower conductive layer, wherein the lower and upper sacrificial patterns include a trench exposing the lower conductive layer, forming mask spacers on sidewalls of the upper and
10 lower sacrificial patterns, using the mask spacers and the upper sacrificial pattern as an etch mask, etching the exposed lower conductive layer to form a lower conductive pattern exposing the substrate, forming a plug conductive layer covering an entire surface of a substrate with the lower conductive pattern, and planarizingly etching the plug conductive layer until the lower
15 sacrificial pattern is exposed, thereby forming a source plug in a gap region between the mask spacers that is connected to the substrate.